

## Silicon NPN Power Transistors

2SC1419

## DESCRIPTION

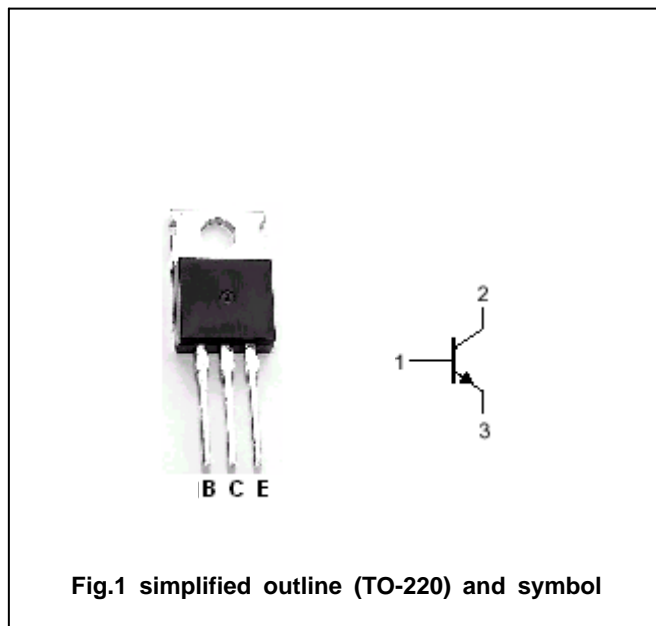
- With TO-220 package
- Large collector power dissipation

## APPLICATIONS

- For medium power amplifier applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings( $T_a=25^{\circ}\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	50	V
$V_{CEO}$	Collector-emitter voltage	Open base	50	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		2	A
$I_{CM}$	Collector current-peak		3	A
$P_C$	Collector power dissipation	$T_C=25^{\circ}\text{C}$	20	W
$T_j$	Junction temperature		150	$^{\circ}\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^{\circ}\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =30mA, I <sub>B</sub> =0	50			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA, I <sub>E</sub> =0	50			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA, I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =1A; I <sub>B</sub> =0.1A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =1A; I <sub>B</sub> =0.1A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =50V; I <sub>E</sub> =0			100	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			100	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =1A; V <sub>CE</sub> =4V	35		320	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A; V <sub>CE</sub> =10V		5		MHz

PACKAGE OUTLINE

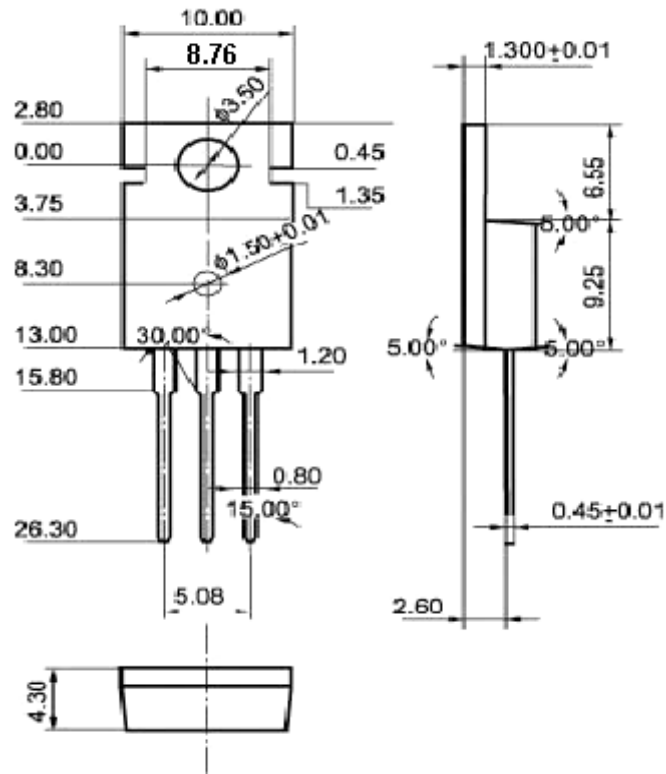


Fig.2 Outline dimensions(unindicated tolerance:  $\pm 0.10$  mm)